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Fig. 1A

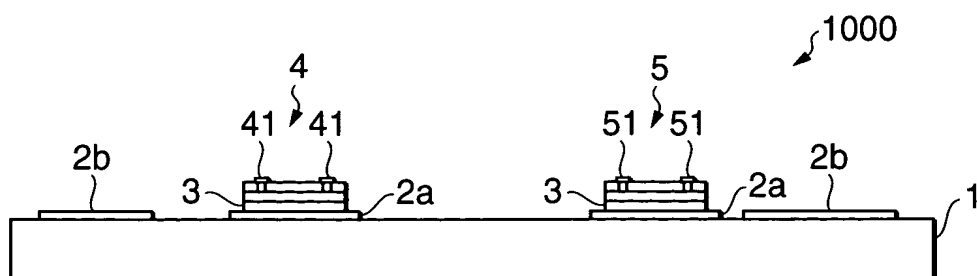


Fig. 1B

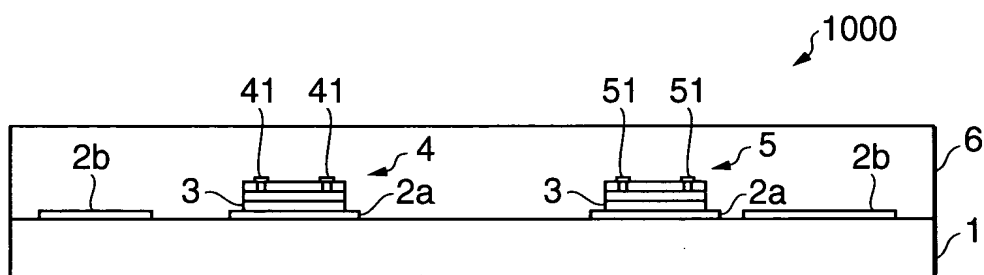


Fig. 1C

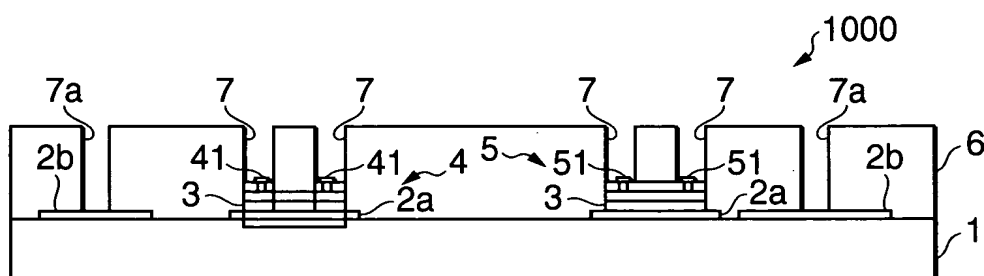


Fig. 1D

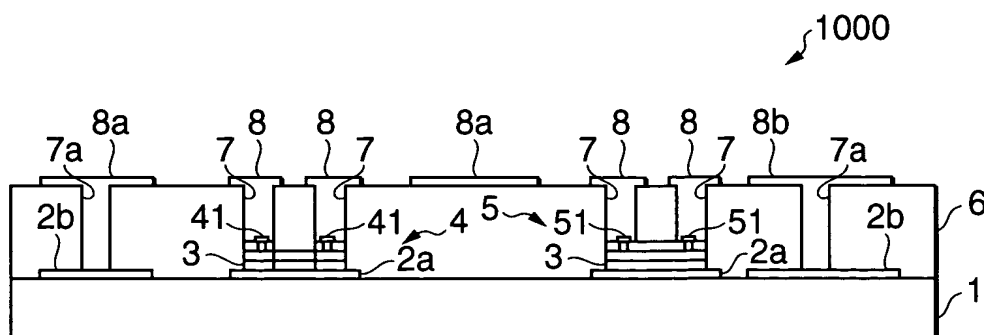
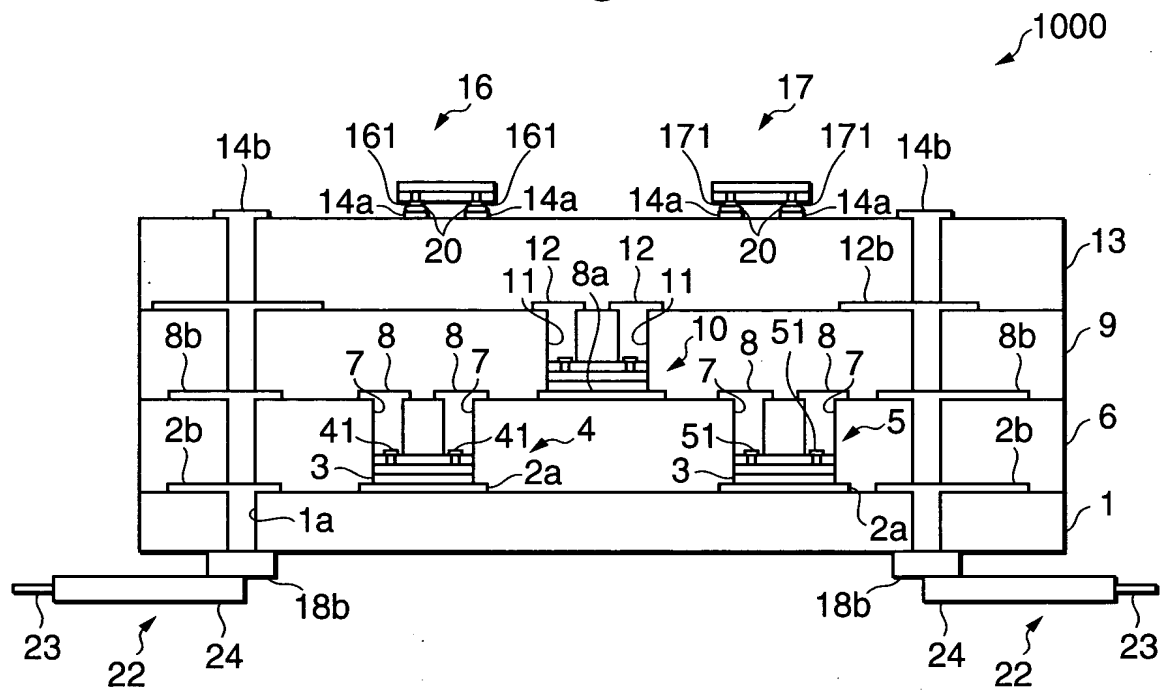


FIG. 1 is a cross-sectional view of a semiconductor device 1000. The device is shown in a cross-section along a line A-A. It features a substrate 1 with a base layer 1a. A central region contains a stack of layers: 2a, 3, 4, 5, 7, 8, 10, 11, 12, 14a, 14b, 16, 17, and 20. The device is flanked by side regions 13 and 14b. The bottom of the device is connected to a terminal 21 via a pad 18b. Various other components are labeled with numbers 1 through 21.

Fig. 3



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Fig. 4A

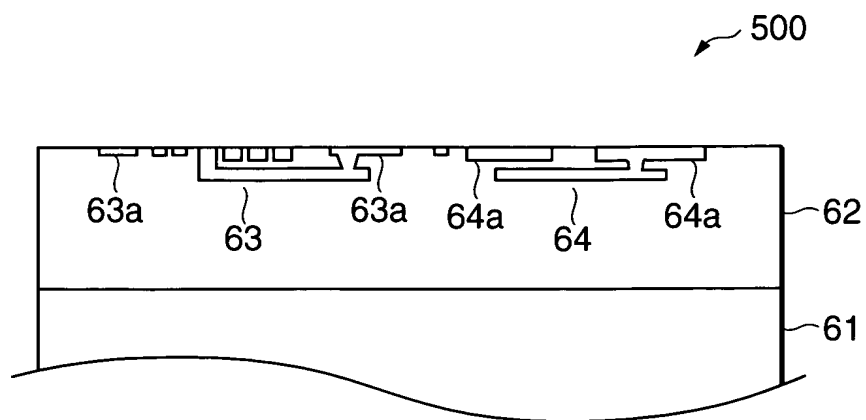


Fig. 4B

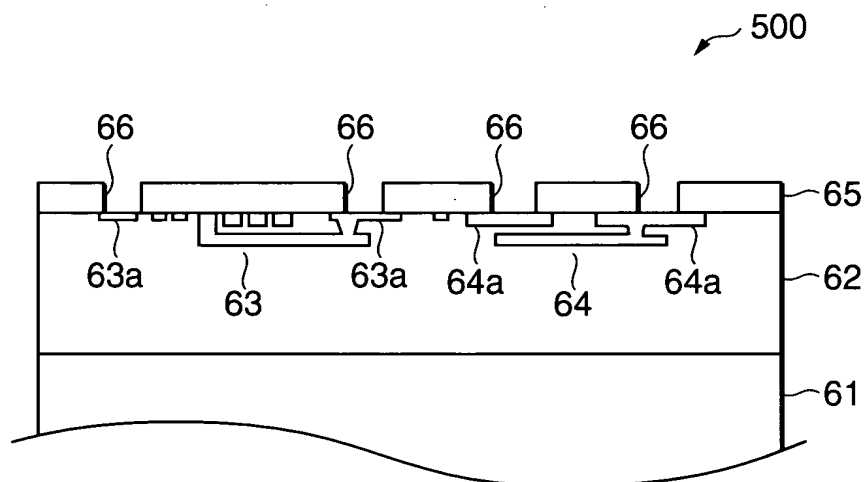
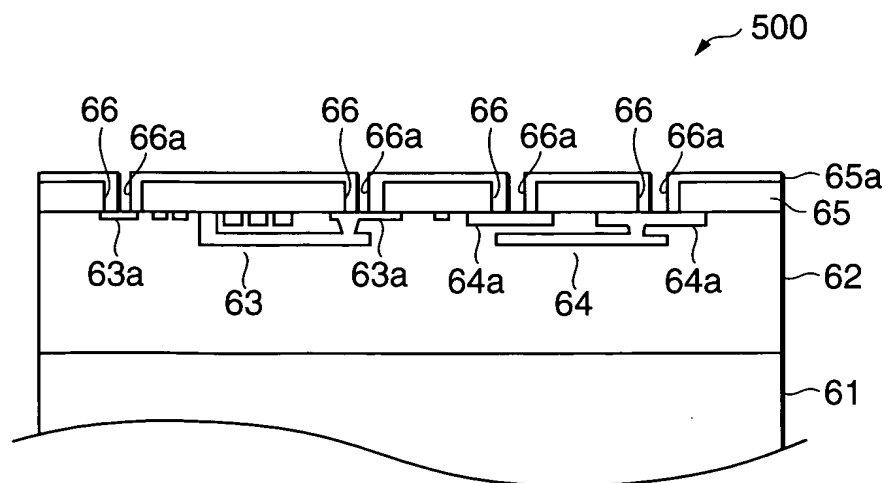


Fig. 4C



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Fig. 5A

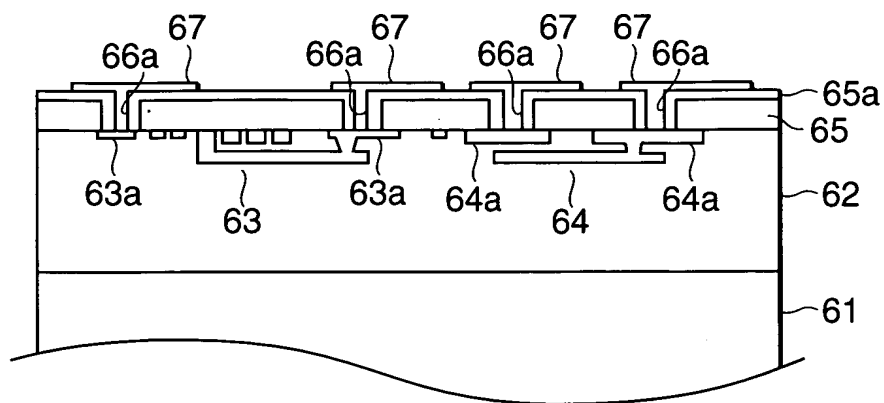
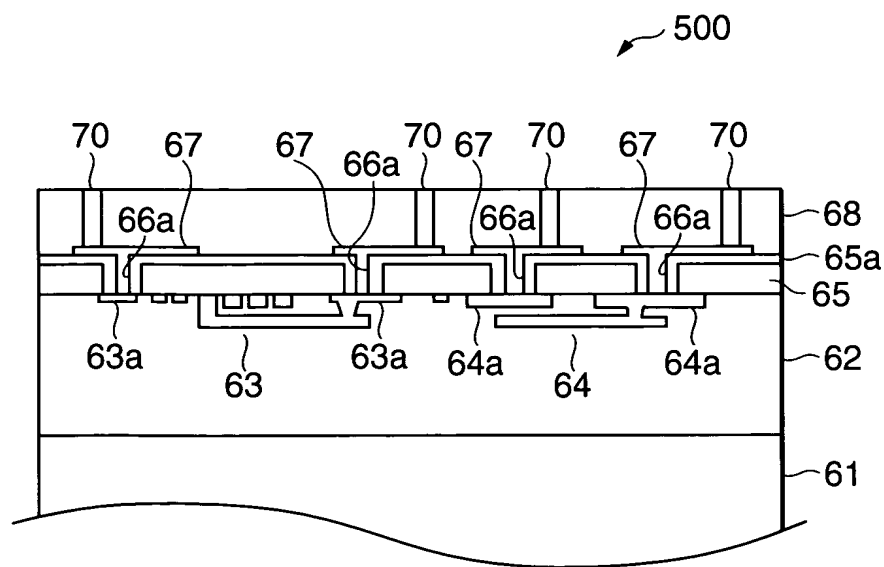
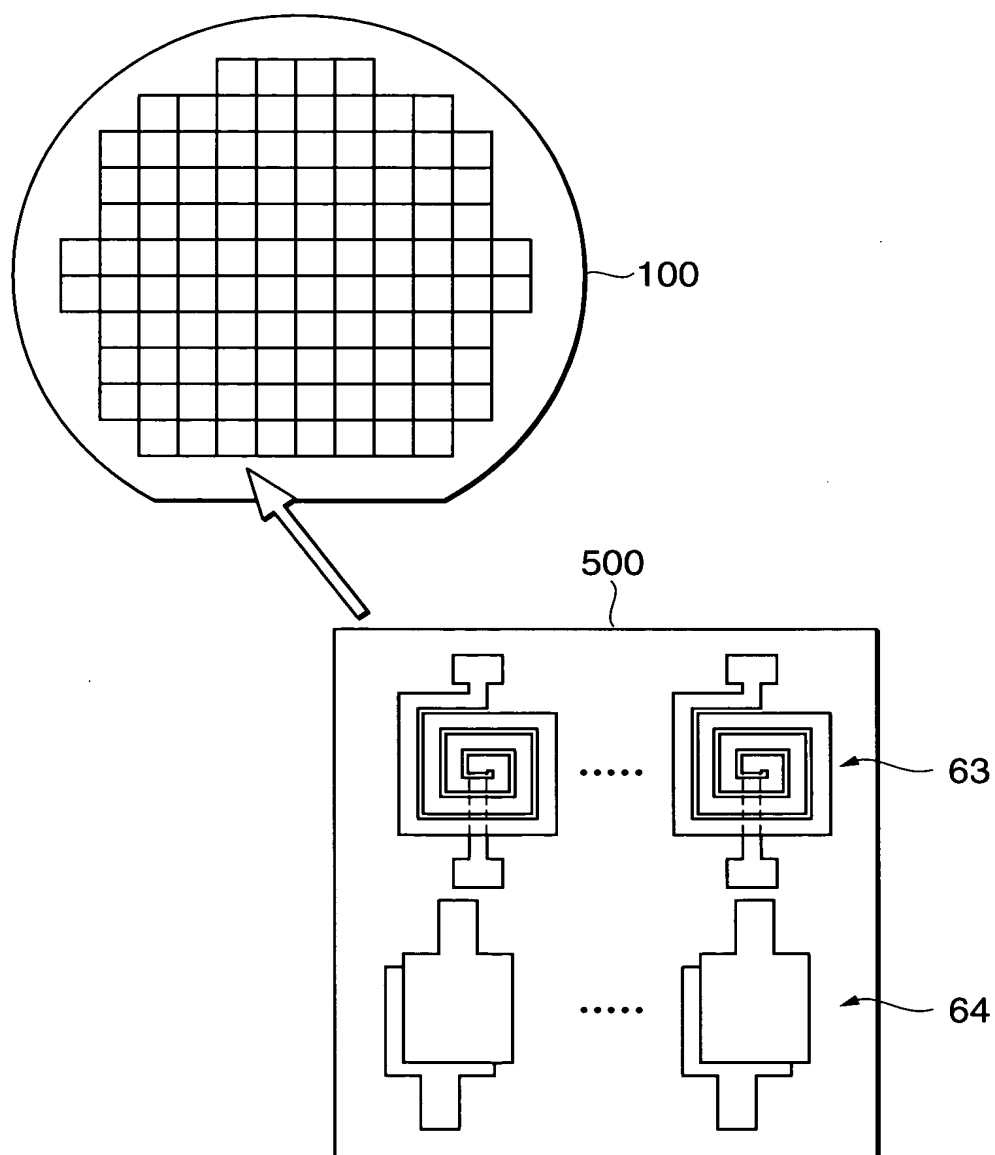


Fig. 5B



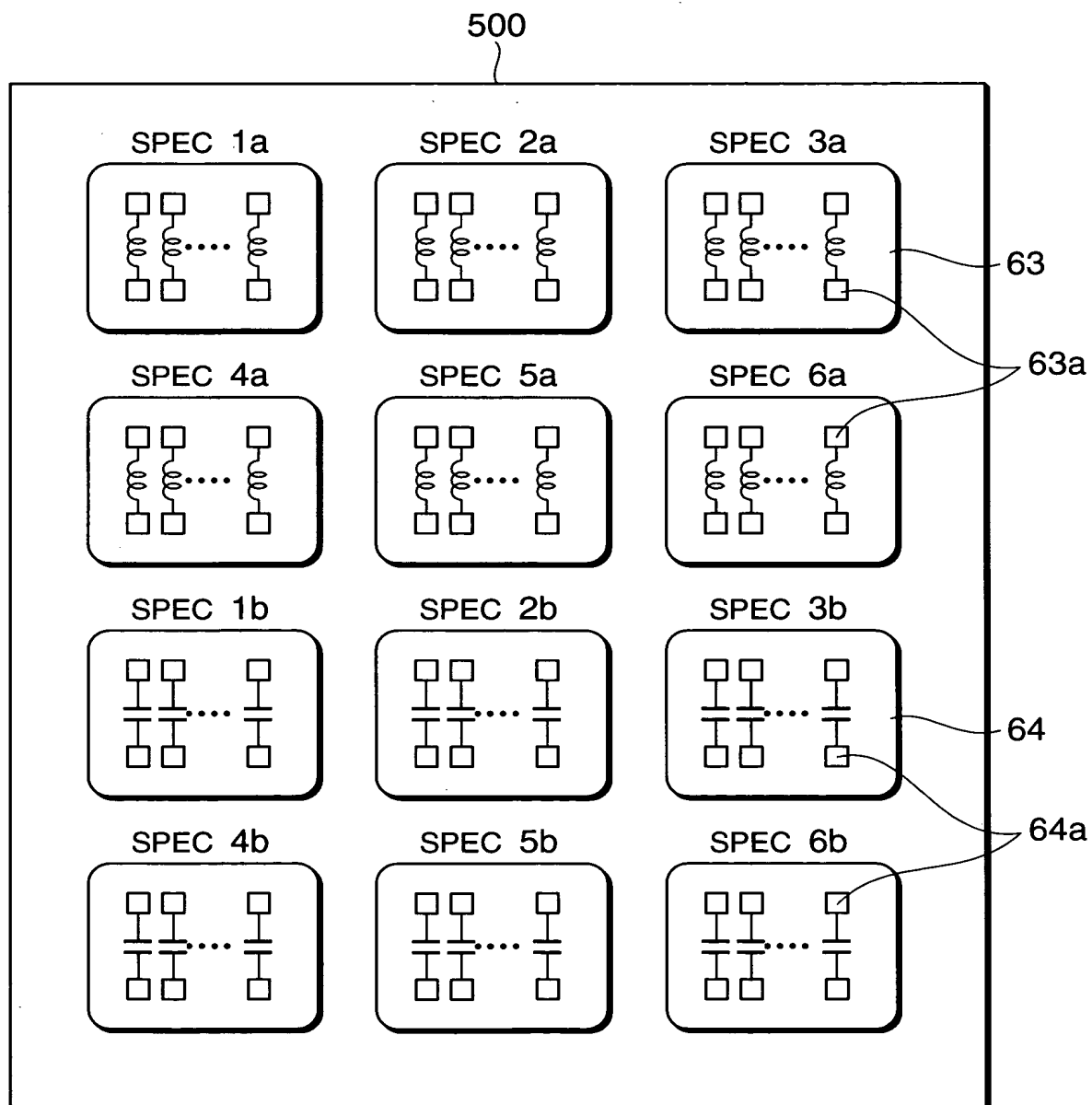
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Fig. 6



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Fig. 7



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Fig. 8

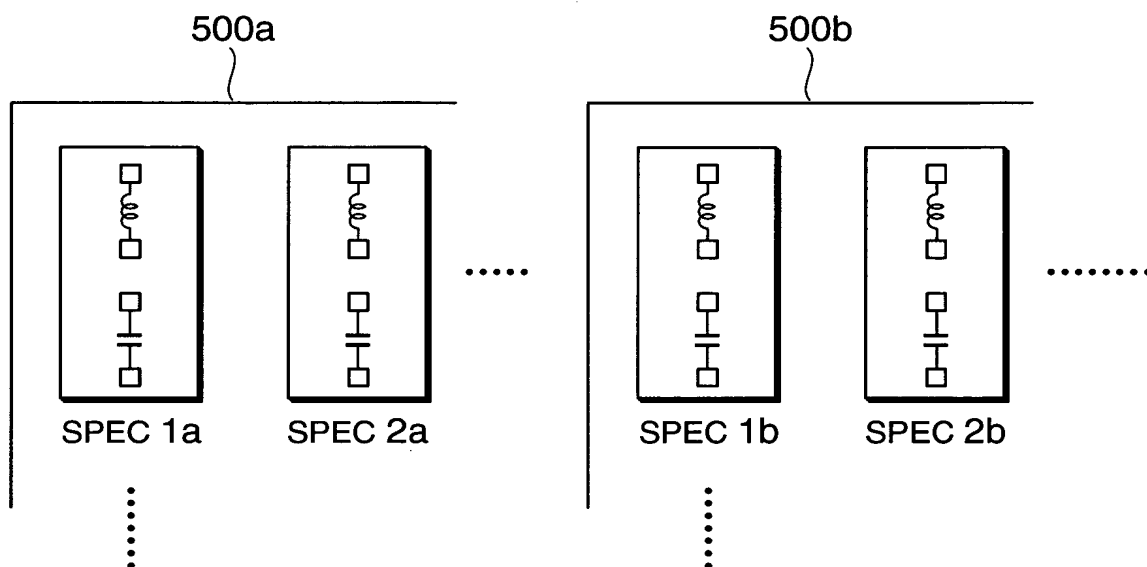
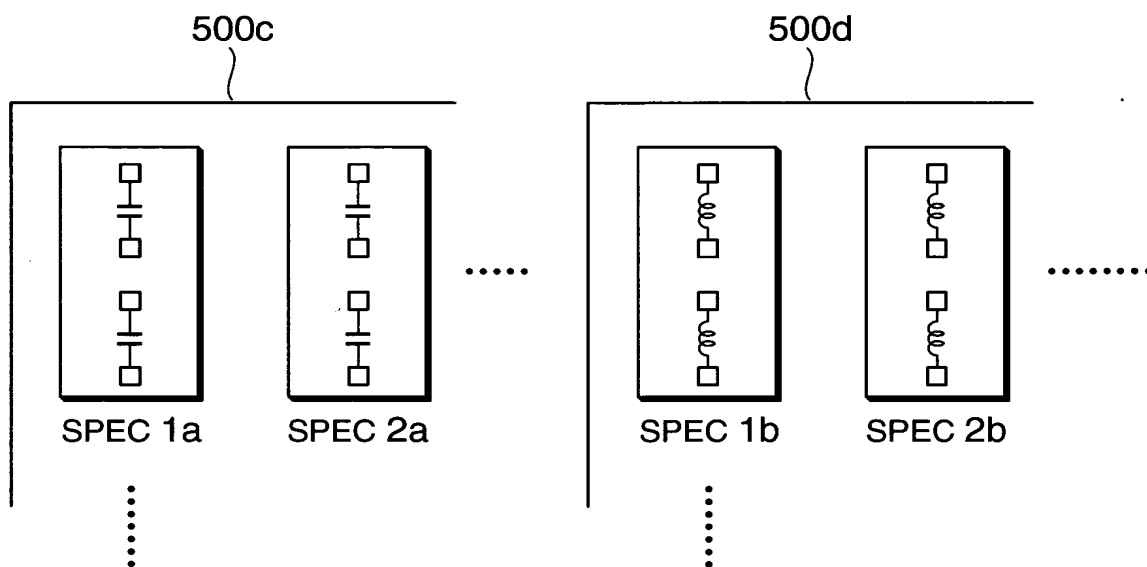


Fig. 9





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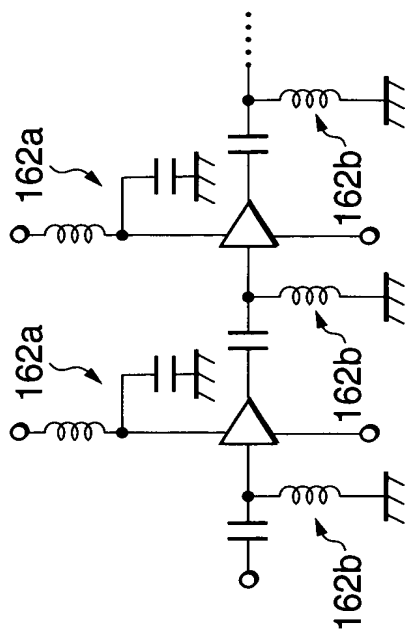


Fig. 10C

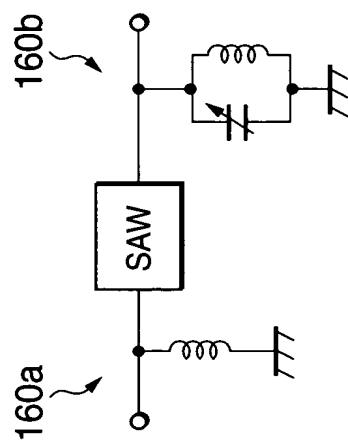


Fig. 10A

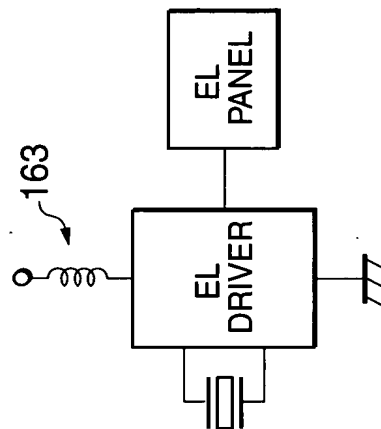


Fig. 10D

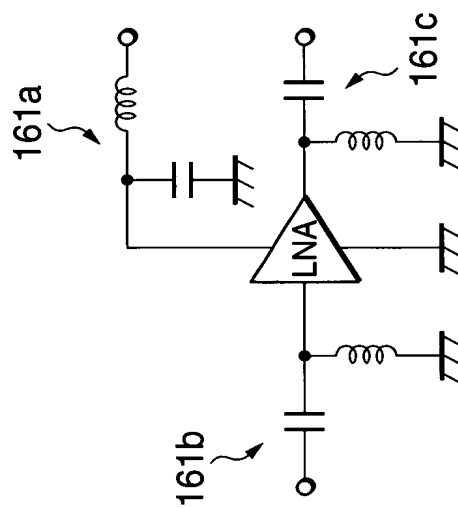


Fig. 10B

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Fig. 11

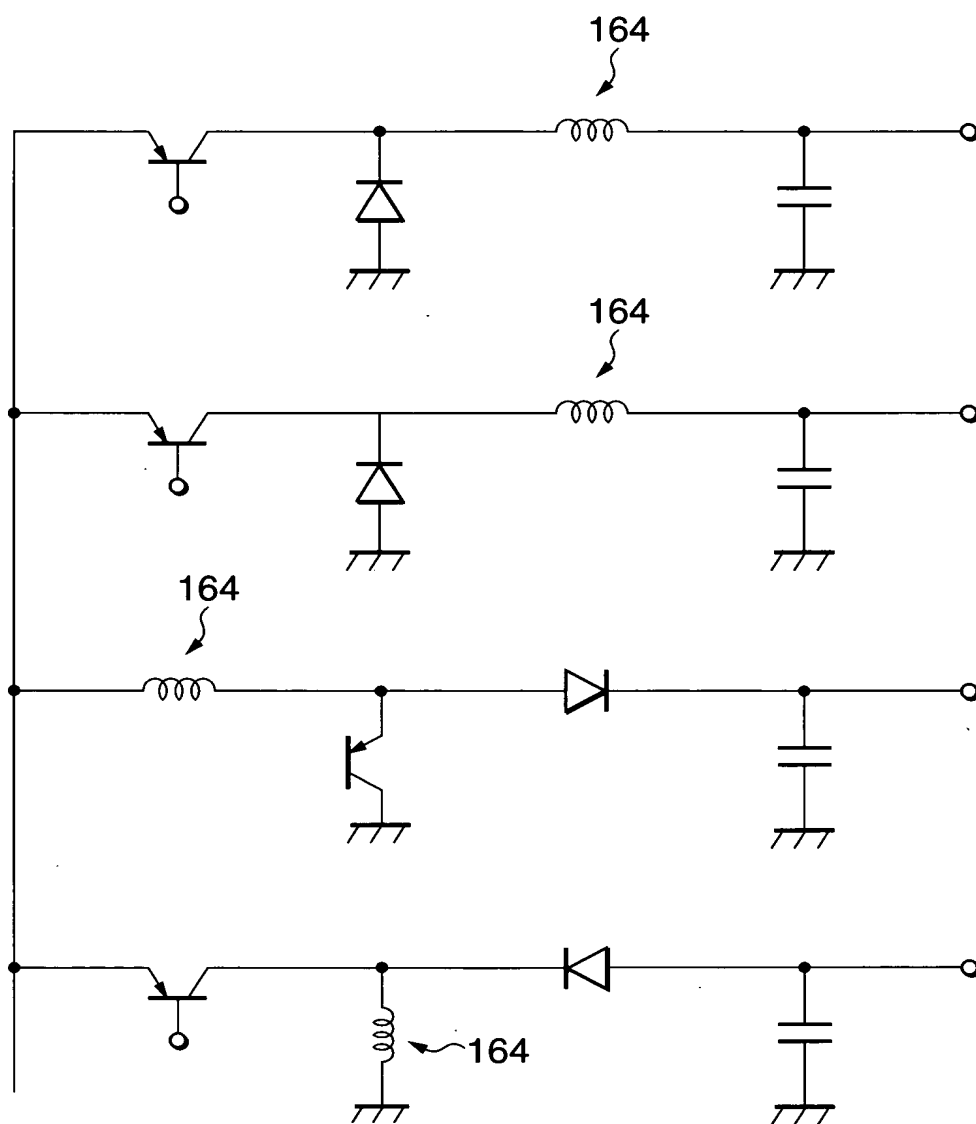


Fig. 12

